

What is claimed is:

1. A method of forming a substrate made of a Group III-V nitride compound including at least one element from Group IIIB elements and at least nitrogen (N) from Group VB elements, wherein the substrate is grown on a growth substrate with a thickness of smaller than or equal to $100\mu\text{m}$, the substrate having a thickness of larger than or equal to $200\mu\text{m}$ and a curvature smaller than or equal to 0.03cm^{-1} , the curvature being caused by a difference in thermal expansion coefficients of the growth base and the substrate.

2. A method of forming a substrate according to claim 1, wherein the growth base made of one selected from a group consisting of sapphire, silicon carbide, spinel, gallium arsenide and silicon is used.

3. A method of forming a substrate according to claim 1, wherein the substrate made of gallium nitride (GaN) is grown.

4. A method of forming a substrate according to claim 1, wherein the substrate is grown by means of hydride vapor phase deposition, halide vapor phase deposition or metal organic chemical vapor deposition.

5. A method of forming a substrate according to claim 1, wherein the substrate is grown while doping impurities.

7. A method of forming a substrate according to claim 1, further comprising a step of removing the growth base.

9. A method of forming a substrate according to claim 7, further comprising a step of forming a protecting film to cover the substrate prior to the step of removing the growth base.

10. A method of forming a substrate according to claim 1, further comprising a step of flattening a surface of the substrate.